PCT WORLD INTELLECTUAL PROPERTY ORGANIZATION
International Bureau

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 7 : H01L 21/66 | A1

(11) International Publication Number: WO 00/04579

(43) International Publication Date: 27 January 2000 (27.01.00)

(21) International Application Number: PCT/US99/16109

(22) International Filing Date: 16 July 1999 (16.07.99)

(30) Priority Data:
10/203230 17 July 1998 (17.07.98) JP

(71) Applicant *(for all designated States except US)*: MEMC ELECTRONIC MATERIALS, INC. [US/US]; 501 Pearl Drive, P.O. Box 8, St. Peters, MO 63376 (US).

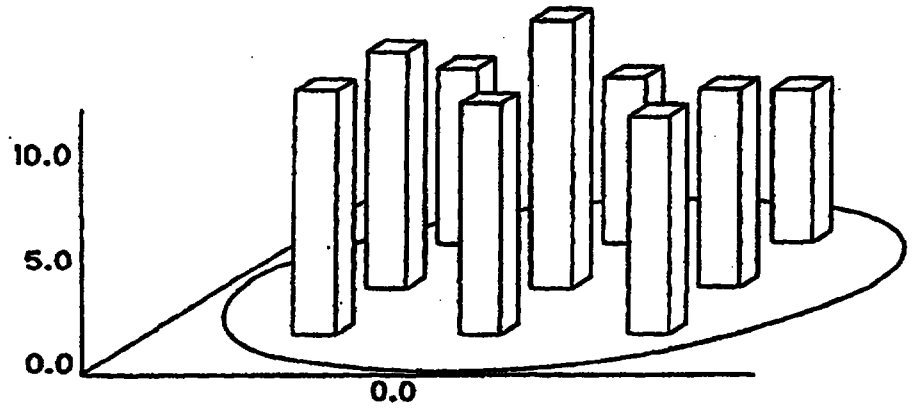
(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: TOMIZAWA, Miwa [-/JP]; Utsunomiya Plant, MEMC Japan Ltd., No. 11-2, Kiyohara Industrial Park, Utsunomiya-city, Tochigi-prefecture (JP). KURODA, Kiyoshi [-/JP]; Utsunomiya Plant, MEMC Japan Ltd., No. 11-2, Kiyohara Industrial Park, Utsunomiya-city, Tochigi-prefecture (JP). NAKAMURA, Norio [-/JP]; Utsunomiya Plant, MEMC Japan Ltd., No. 11-2, Kiyohara Industrial Park, Utsunomiya-city, Tochigi-prefecture (JP).

(74) Agents: HEJLEK, Edward, J. et al.; Senniger, Powers, Leavitt & Roedel, 16th floor, One Metropolitan Square, St. Louis, MO 63102 (US).

(81) Designated States: CN, JP, KR, SG, US, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

Published
With international search report.
Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.

(54) Title: PROCESS FOR MAPPING METAL CONTAMINANT CONCENTRATION ON A SILICON WAFER SURFACE



(57) Abstract

A process is provided for preparing a reference wafer having a surface which is substantially uniformly contaminated with one or more metals of interest and which is suitable for use in the calibration of a total reflection fluorescent X-ray apparatus. The process comprises immersing a virgin wafer in a treatment solution obtained by mixing an aqueous stock solution containing a water-soluble salt of a metallic contaminant of interest with an organic solvent, and then drying thus immersed wafer.